TENTATIVE

TOSHIBA Photocoupler Photo-Diode

TLP722

The TOSHIBA TLP722 consists of a photo-diode optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP (DIP4).

TLP722: Single circuit

- Cathode-anode voltage: 30V (max)
- Current transfer ratio: 0.1% (min)
- Input / output isolation voltage: 4000V_{rms} (min)
- Operating temperature range: -55~100°C
- Storage temperature range: -55~125°C
- UL recognized: UL1577, E67349
- VDE approved: VDE0884

Maximum operating insulation voltage: 890 VPK Maximum permissible over voltage: 8000 VPK

(Note): When a VDE0884 approved type is needed, please designate the "Option (D4)"

• SEMKO approved product: SS EN60950,

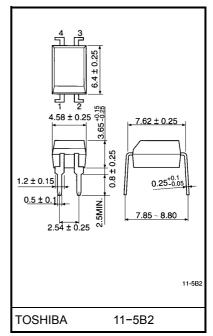
approved No. 9808324 / 01

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• Construction mechanical rating

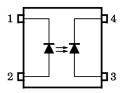
	TLP722 type	TLP722F type
Creepage distance	7.0 mm	8.0 mm
Clearance	7.0 mm	8.0 mm
Insulation thickness	0.4 mm	0.4 mm

Unit in mm



Weight: 0.28 g

Pin Configuration (top view)



1 : LED CATHODE

2: LED ANODE

3 : DETECTOR ANODE 4 : DETECTOR CATHODE



Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
LED	Forward current	l _F	25	mA
	Forward current derating	ΔI _F / °C	–0.45 (Ta ≥ 70°C)	mA / °C
	Pulse forward current	I _{FP}	1 (1µs pulse, 1000 pps)	mA
	Pulse forward current	I _{FTP}	1 (100µs pulse, 1000 pps)	Α
	Reverse voltage	V_{R}	5	V
Detector	Cathode-anode voltage	V _{KAO}	30	V
	Anode-cathode voltage	V_{AKO}	0.5	V
	Photodiode output current	I _{PB}	100	μΑ
	Junction temperature	Tj	125	°C
Sto	rage temperature range	T _{stg}	-55~125	°C
Оре	erating temperature range	T _{opr}	−55~100	°C
Lea	d soldering temperature (10 s)	T _{sol}	260 (10s)	°C
Isol	ation voltage	BVS	4000 (AC, 1min., R.H. 60%)	V _{rms}

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	V _F	I _F = 16 mA	_	1.65	1.85	V
ED	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	-	30		pF
Detector	Cathode–anode breakdown voltage	V _(BR) KAO	I _{KA} = 0.1 mA	30	1	1	V
	Anode-cathode breakdown voltage	V _{(BR)AKO}	I _{AK} = 0.1 mA	0.5	_	1	V
	Dark current I _{le}	l	V _{KA} = 10 V	1	_	50	nA
		l _{leak}	V _{KA} = 10 V, Ta = 85°C	1	_	1	μA
	Photodaiode output current	I _{PB}	V = 10 mA, V _{KA} = 5 V	10	_	50	μΑ
	Capacitance	C _{AK}	V = 0, f = 1 MHz	_	10	_	pF

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF	
Isolation resistance	R _S	V _S = 500 V	1×10 ¹²	10 ¹⁴	_	Ω	
	on voltage BV _S	AC, 1 minute	4000	_	_	V	
Isolation voltage		AC, 1 second, in oil	_	10000	_	V _{rms}	
		DC, 1 minute, in oil	_	10000	_	V_{dc}	

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